

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =250μA, V _{GS} =0V	30			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =30V, V _{GS} =0V T _J =55°C			1 5	μA
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} = ±20V			100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1.5	1.98	2.5	V
I _{D(ON)}	On state drain current	V _{GS} =10V, V _{DS} =5V	110			A
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =15A T _J =125°C		6.4 10	7.7 12	mΩ
		V _{GS} =4.5V, I _D =12A		8.6	10.8	mΩ
g _{FS}	Forward Transconductance	V _{DS} =5V, I _D =15A		45		S
V _{SD}	Diode Forward Voltage	I _S =1A, V _{GS} =0V		0.74	1	V
I _S	Maximum Body-Diode Continuous Current				4	A
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =15V, f=1MHz	920	1150	1380	pF
C _{oss}	Output Capacitance		125	180	235	pF
C _{rss}	Reverse Transfer Capacitance		60	105	150	pF
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz	0.55	1.1	1.65	Ω
SWITCHING PARAMETERS						
Q _{g(10V)}	Total Gate Charge	V _{GS} =10V, V _{DS} =15V, I _D =15A	16	20	24	nC
Q _{g(4.5V)}	Total Gate Charge		7.6	9.5	11.4	nC
Q _{gs}	Gate Source Charge		2	2.7	3.2	nC
Q _{gd}	Gate Drain Charge		3	5	7	nC
t _{D(on)}	Turn-On DelayTime	V _{GS} =10V, V _{DS} =15V, R _L =1Ω, R _{GEN} =3Ω		6.5		ns
t _r	Turn-On Rise Time			2		ns
t _{D(off)}	Turn-Off DelayTime			17		ns
t _f	Turn-Off Fall Time			3.5		ns
t _{rr}	Body Diode Reverse Recovery Time	I _F =15A, dI/dt=500A/μs	7	8.7	10.5	ns
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =15A, dI/dt=500A/μs	11	13.5	16	nC

A. The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25° C. The value in any given application depends on the user's specific board design.

B. The power dissipation P_D is based on T_{J(MAX)}=150° C, using ≤ 10s junction-to-ambient thermal resistance.

C. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150° C. Ratings are based on low frequency and duty cycles to keep initial T_J=25° C.

D. The R_{θJA} is the sum of the thermal impedance from junction to lead R_{θJL} and lead to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-ambient thermal impedance which is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, assuming a maximum junction temperature of T_{J(MAX)}=150° C. The SOA curve provides a single pulse rating.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

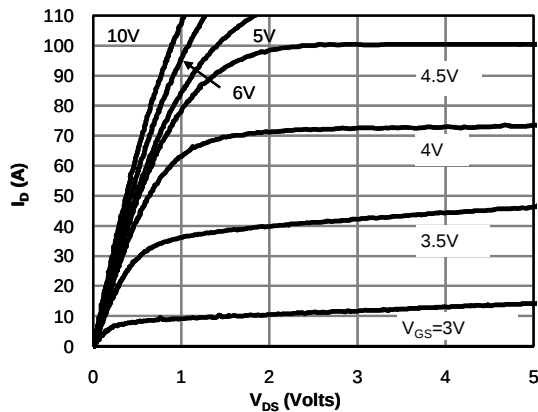


Figure 1: On-Region Characteristics (Note E)

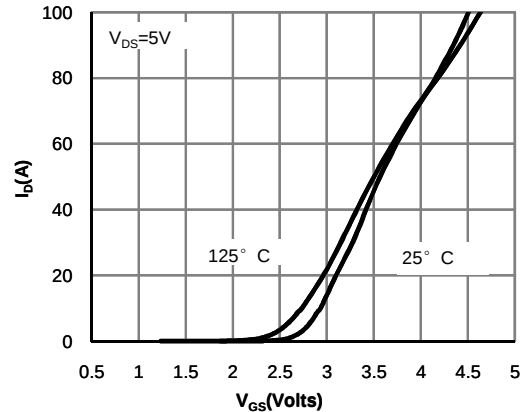


Figure 2: Transfer Characteristics (Note E)

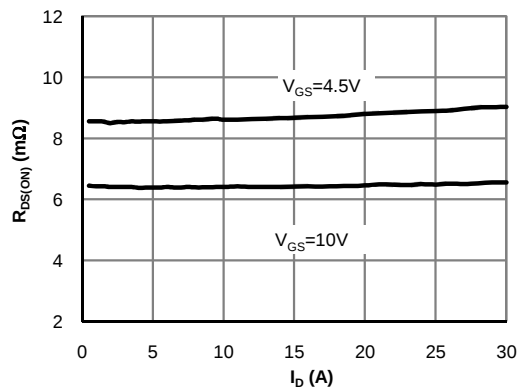


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

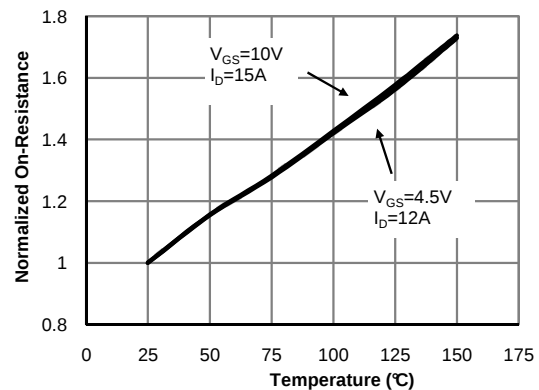


Figure 4: On-Resistance vs. Junction Temperature (Note E)

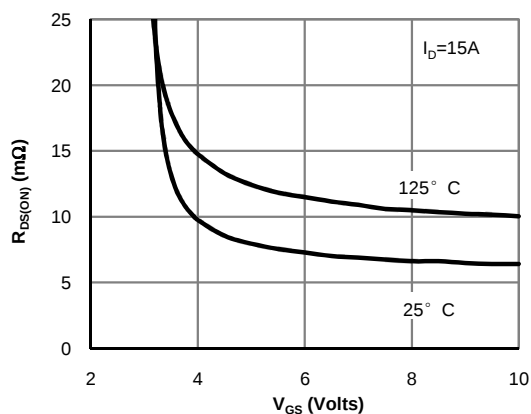


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

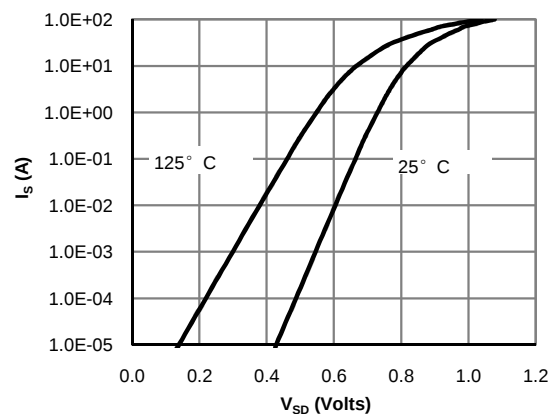
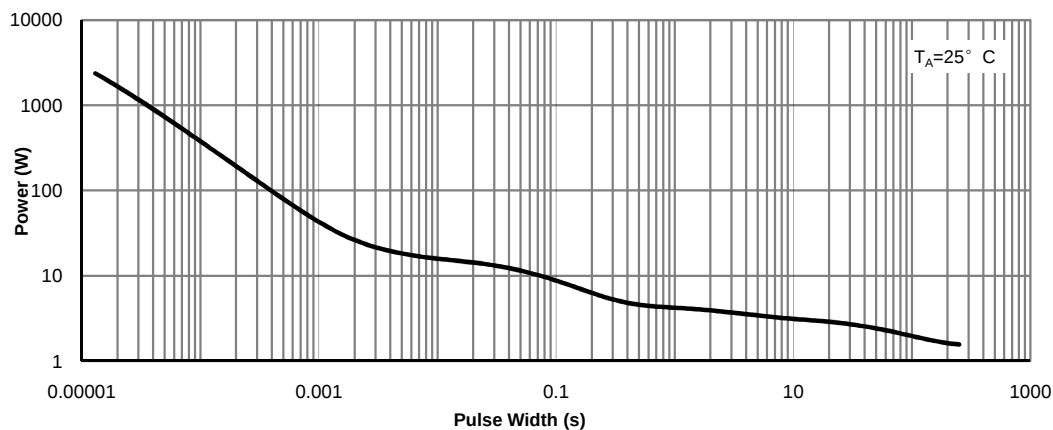
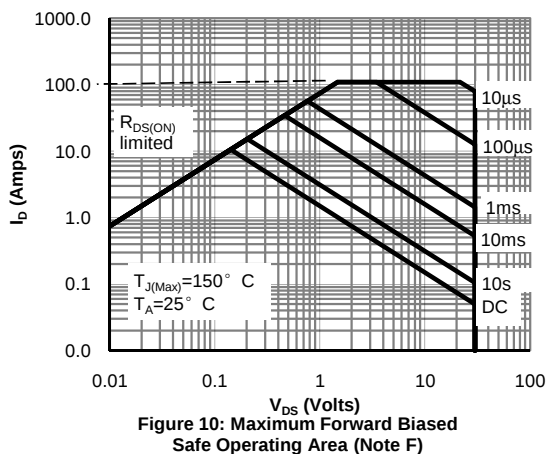
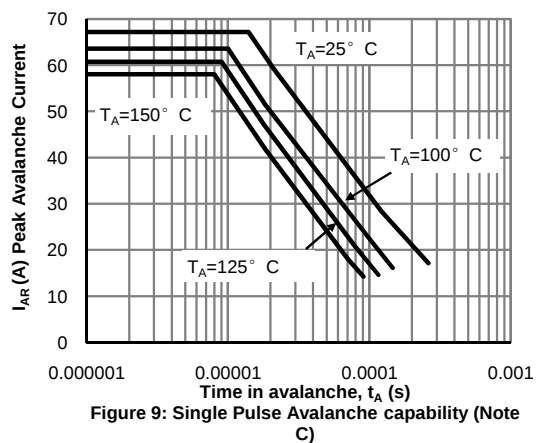
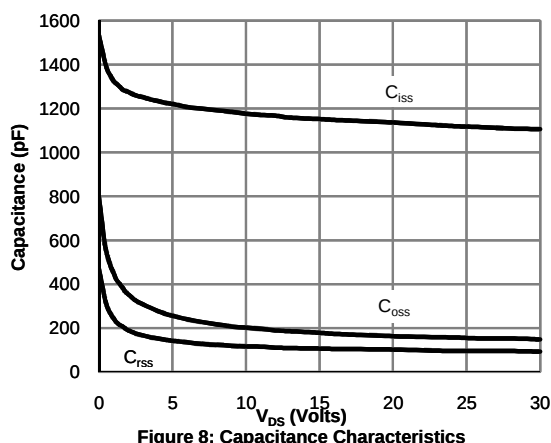
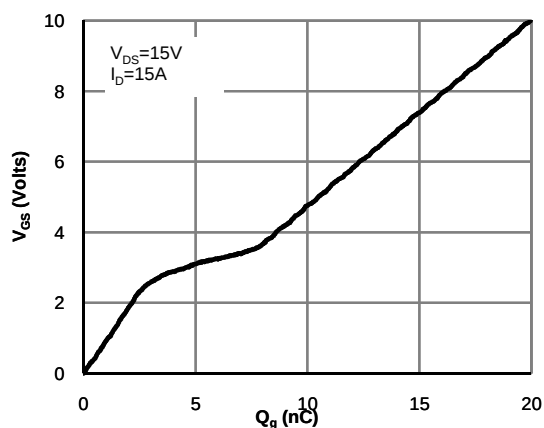


Figure 6: Body-Diode Characteristics (Note E)

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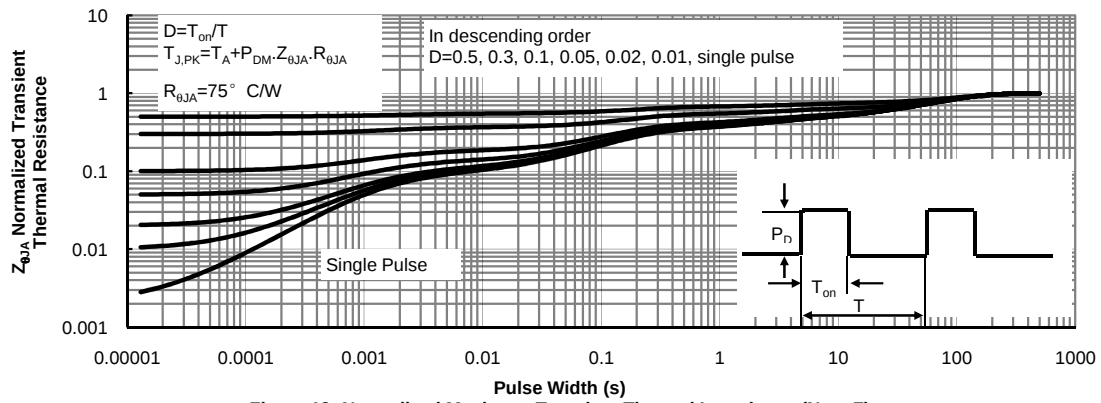
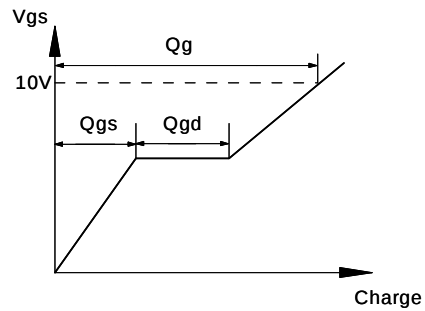
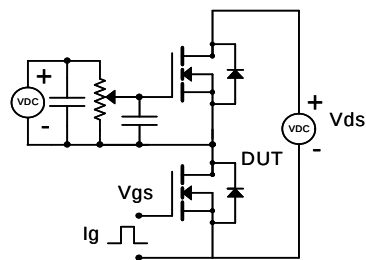
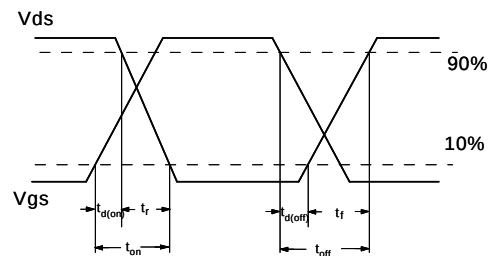
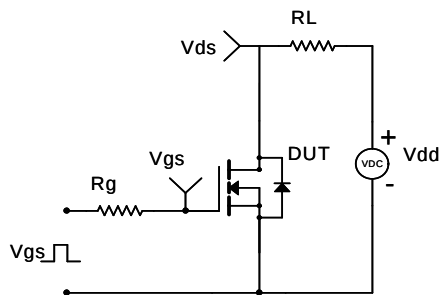


Figure 12: Normalized Maximum Transient Thermal Impedance (Note F)

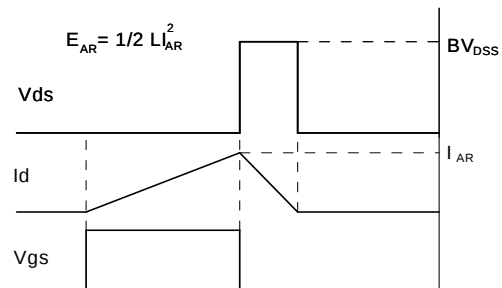
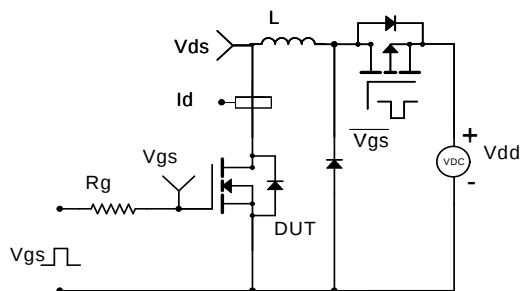
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms

